



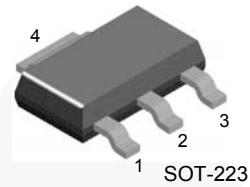
November 2014

BCP69

PNP General-Purpose Amplifier

Description

This device is designed for general-purpose medium-power amplifiers and switches requiring collector currents to 1.0 A. Sourced from process 77.



1. Base 2,4. Collector 3. Emitter

Ordering Information

Part Number	Marking	Package	Packing Method
BCP69	BCP69	SOT-223 4L	Tape and Reel

Absolute Maximum Ratings^{(1),(2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{CBO}	Collector-Base Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current - Continuous	-1.5	A
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Notes:

1. These ratings are based on a maximum junction temperature of 150°C .
2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics⁽³⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P_D	Total Device Dissipation	1.0	W
	Derate Above 25°C	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	$^\circ\text{C}/\text{W}$

Note:

3. Device is mounted on FR-4 PCB 36 mm × 18 mm × 1.5 mm; mounting pad for the collector lead minimum 6 cm².

Electrical Characteristics⁽⁴⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -10\text{ mA}$, $I_B = 0$	-20			V
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = -1.0\text{ mA}$, $I_E = 0$	-30			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -100\ \mu\text{A}$, $I_C = 0$	-5.0			V
I_{CBO}	Collector-Base Cut-Off Current	$V_{CB} = -25\text{ V}$, $I_E = 0$			-100	nA
		$V_{CB} = -25\text{ V}$, $I_E = 0$, $T_J = 150^\circ\text{C}$			-10	μA
I_{EBO}	Emitter-Base Cut-Off Current	$V_{EB} = -5.0\text{ V}$, $I_C = 0$			-100	nA
h_{FE}	DC Current Gain	$I_C = -5\text{ mA}$, $V_{CE} = -1.0\text{ V}$	50			
		$I_C = -500\text{ mA}$, $V_{CE} = -1.0\text{ V}$	85		375	
		$I_C = -1.0\text{ A}$, $V_{CE} = -1.0\text{ V}$	60			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1.0\text{ A}$, $I_B = -100\text{ mA}$			-0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1.0\text{ A}$, $V_{CE} = -1.0\text{ V}$			-1.0	V
C_{cb}	Collector-Base Capacitance	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1.0\text{ MHz}$			30	pF
h_{fe}	Small-Signal Current Gain	$I_C = -50\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 20\text{ MHz}$	2.5			

Note:

4. Pulse test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2.0\%$

Typical Performance Characteristics

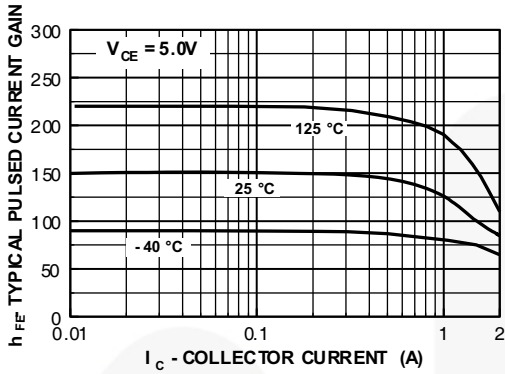


Figure 1. Typical Pulsed Current Gain vs. Collector Current

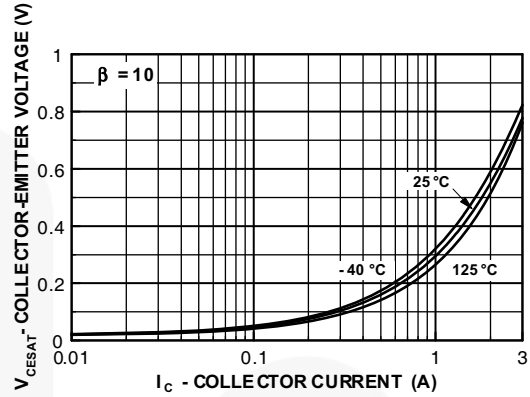


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

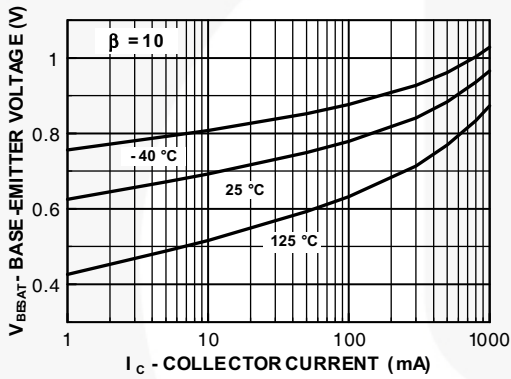


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

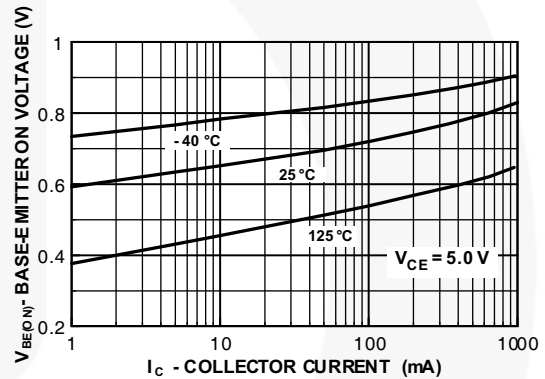


Figure 4. Base Emitter On Voltage vs. Collector Current

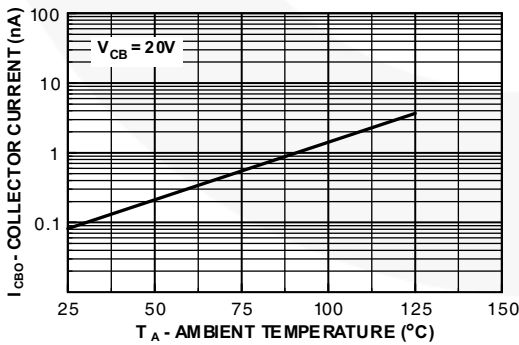


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

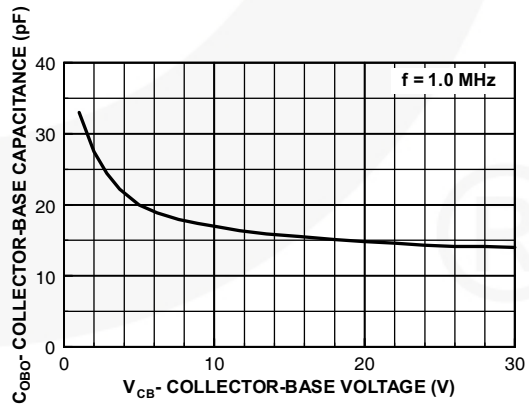


Figure 6. Collector-Base Capacitance vs. Collector-Base Voltage

Typical Performance Characteristics (Continued)

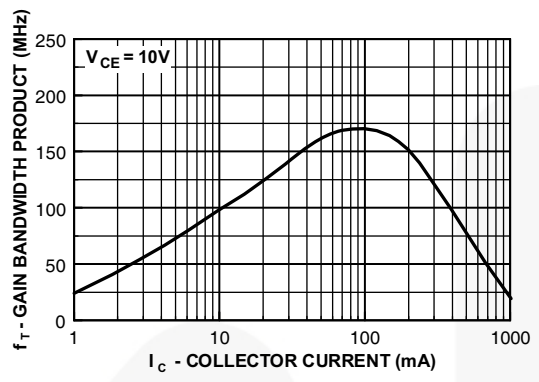


Figure 7. Gain Bandwidth Product vs. Collector Current

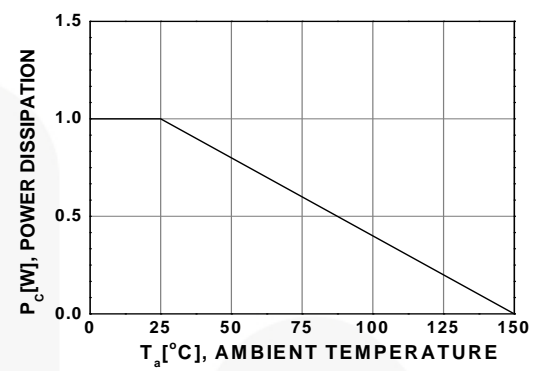
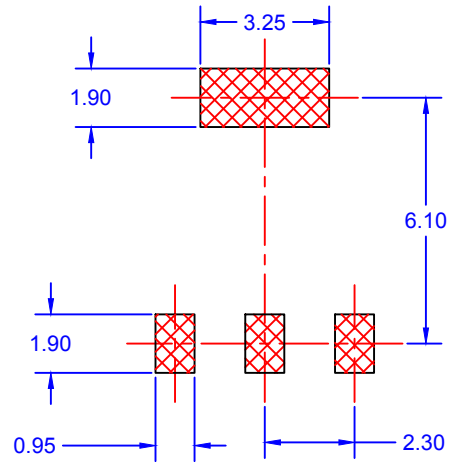
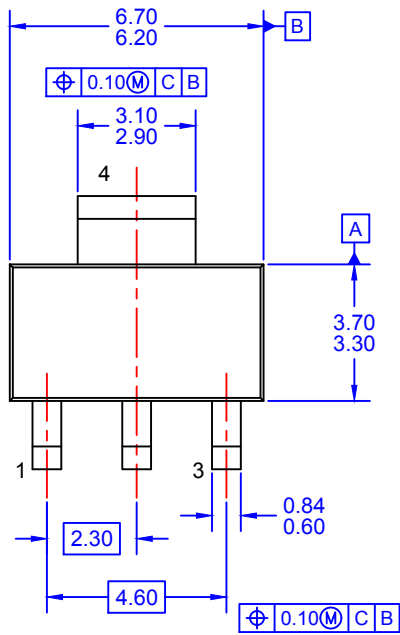
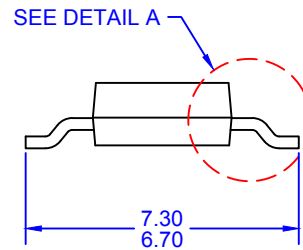
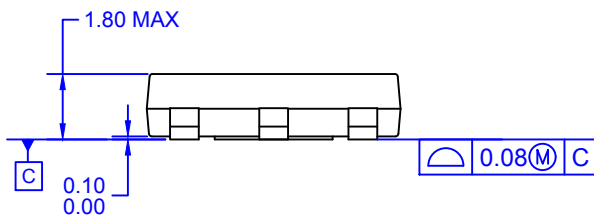


Figure 8. Power Dissipation vs. Ambient Temperature

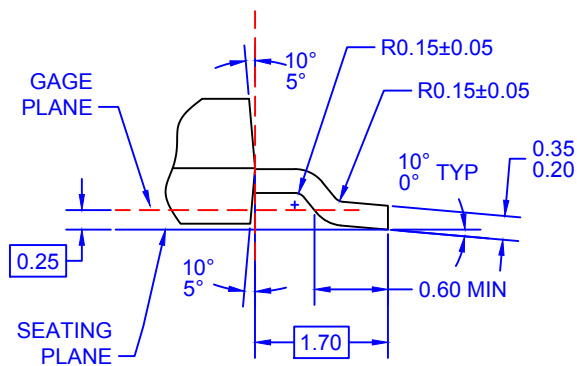




LAND PATTERN RECOMMENDATION



- NOTES: UNLESS OTHERWISE SPECIFIED
 A) DRAWING BASED ON JEDEC REGISTRATION TO-261C, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 E) LANDPATTERN NAME: SOT230P700X180-4BN
 F) DRAWING FILENAME: MKT-MA04AREV3



DETAIL A
SCALE: 2:1



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